

FORM PTO - 1449 INFORMATION DISCLOSURE STATEMENT				ATTORNEY DOCKET NO.: ASC-063 APPLICANT(S): Currie <i>et al.</i> SERIAL NO.: 10/696,994 FILING DATE: October 30, 2003 GROUP: 281+2823					
U.S. PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
WB	A1	5,442,205	08/15/1995	Brasen <i>et al.</i>	257	191	08/09/1993		
WB	A2	5,726,087	03/10/1998	Tseng <i>et al.</i>	438	261	06/09/1994		
WB	A3	5,780,922	07/14/1998	Mishra <i>et al.</i>	257	616	11/27/1996		
WB	A4	6,107,653	08/22/2000	Fitzgerald	257	191	06/23/1998		
WB	A5	6,284,615 B1	09/04/2001	Pinto <i>et al.</i>	438	336	06/16/1999		
WB	A6	US2002/0068393 A1	06/06/2002	Fitzgerald <i>et al.</i>	438	172	08/06/2001		
WB	A7	US2003/0230233 A1	12/18/2003	Fitzgerald <i>et al.</i>	117	89	03/19/2003		
WB	A8	US2004/0031979 A1	02/19/2004	Lochtefeld <i>et al.</i>	257	233	06/06/2003		
FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
WB	B1	01/022482 A1	03/29/2001	WO	X	X	X	N	Y
WB	B2	03/001607 A1	01/03/2003	WO	X	X	X	N	Y
OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
WB	C1	Currie <i>et al.</i> , "Carrier Mobilities and Process Stability of Strained Si <i>n</i> - and <i>p</i> -MOSFETs on SiGe virtual substrates," <i>J. Vac. Sci. Technol. B</i> , 19(6):2268-2279 (2001).							
WB	C2	Kummer <i>et al.</i> , "Low Energy Plasma Enhanced Chemical Vapor Deposition," <i>Mat. Sci. & Eng. B89</i> , 288-295 (2002).							
WB	C3	Leitz <i>et al.</i> , "Hole mobility enhancements and alloy scattering-limited mobility in tensile strained Si/SiGe surface channel metal-oxide-semiconductor field-effect transistors," <i>Journal of Applied Physics</i> , 92(7):3745-3751 (2002).							
WB	C4	Lucovsky <i>et al.</i> , "Low-temperature plasma-assisted oxidation of Si: a new approach for creation of device-quality Si-SiO ₂ interfaces with deposited dielectrics for applications in Si MOSFET technologies," <i>Journal of Non-Crystalline Solids</i> , 179 354-366 (1994).							
WB	C5	Pal <i>et al.</i> , "Gd ₂ O ₃ , Ga ₂ O ₃ (Gd ₂ O ₃), Y ₂ O ₃ , and Ga ₂ O ₃ , as high- <i>k</i> gate dielectrics on SiGe: A comparative study," <i>Journal of Applied Physics</i> , 90(8):4103-4107 (2001).							
WB	C6	Sugii <i>et al.</i> , "Role of Si _{1-x} Ge _x buffer layer on mobility enhancement in a strained-Si <i>n</i> -channel metal-oxide-semiconductor field-effect transistor," <i>Applied Physics Letters</i> , 75(19):2948-2950 (1999).							
WB	C7	Invitation to Pay Additional Fees for International Application No. PCT/US 03/34576 mailed on December 17, 2004, 7 pages.							
EXAMINER William M. Branstetter				DATE CONSIDERED 28 APR 05					